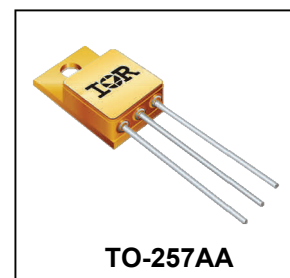


**POWER MOSFET**  
**THRU-HOLE (TO-257AA)**
**100V, N-CHANNEL**  
**HEXFET® MOSFET TECHNOLOGY**
**Product Summary**

| Part Number | RDS(on) | I <sub>D</sub> | Eyelets |
|-------------|---------|----------------|---------|
| IRFY140C    | 0.077Ω  | 16A*           | Ceramic |
| IRFY140CM   | 0.077Ω  | 16A*           | Ceramic |


**Description**

HEXFET® MOSFET technology is the key to IR HiRel advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high trans conductance. HEXFET® transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain capacitance.

**Features**

- Simple Drive Requirements
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets
- Ideally Suited For Space Level Applications
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

**Absolute Maximum Ratings**

| Symbol  | Parameter   | Value                                    | Units |
|---|---|--|-------|
| I <sub>D1</sub> @ V <sub>GS</sub> = 10V, T <sub>C</sub> = 25°C  | Continuous Drain Current                            | 16*                                      | A     |
| I <sub>D2</sub> @ V <sub>GS</sub> = 10V, T <sub>C</sub> = 100°C | Continuous Drain Current                            | 16*                                      |       |
| I <sub>DM</sub> @ T <sub>C</sub> = 25°C                         | Pulsed Drain Current ①                              | 64                                       |       |
| P <sub>D</sub> @ T <sub>C</sub> = 25°C                          | Maximum Power Dissipation                           | 100                                      | W     |
|   | Linear Derating Factor                              | 0.8                                      | W/°C  |
| V <sub>GS</sub>   | Gate-to-Source Voltage                              | ± 20                                     | V     |
| E <sub>AS</sub>   | Single Pulse Avalanche Energy ②                     | 230                                      | mJ    |
| I <sub>AR</sub>   | Avalanche Current ①                                 | 16*                                      | A     |
| E <sub>AR</sub>   | Repetitive Avalanche Energy ①                       | 10                                       | mJ    |
| dv/dt   | Peak Diode Recovery ③                               | 5.5                                      | V/ns  |
| T <sub>J</sub><br>T <sub>STG</sub>                              | Operating Junction and<br>Storage Temperature Range | -55 to + 150                             | °C    |
|   | Lead Temperature                                    | 300(0.063in./1.6mm from case for 10 sec) |       |
|   | Weight  | 4.3 (Typical)                            |       |

\*Current is limited by package  
For footnotes refer to the page 2.

### Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)

| Symbol                              | Parameter                            | Min. | Typ. | Max.  | Units | Test Conditions   |
|-------------------------------------|--------------------------------------|------|------|-------|-------|---|
| BV <sub>DSS</sub>                   | Drain-to-Source Breakdown Voltage    | 100  | —    | —     | V     | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA  |
| ΔBV <sub>DSS</sub> /ΔT <sub>J</sub> | Breakdown Voltage Temp. Coefficient  | —    | 0.1  | —     | V/°C  | Reference to 25°C, I <sub>D</sub> = 1.0mA   |
| R <sub>DS(on)</sub>                 | Static Drain-to-Source On-Resistance | —    | —    | 0.077 | Ω     | V <sub>GS</sub> = 10V, I <sub>D2</sub> = 16A ④  |
| V <sub>GS(th)</sub>                 | Gate Threshold Voltage               | 2.0  | —    | 4.0   | V     | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                    |
| G <sub>fs</sub>                     | Forward Transconductance             | 9.1  | —    | —     | S     | V <sub>DS</sub> = 15V, I <sub>D2</sub> = 16A ④  |
| I <sub>DSS</sub>                    | Zero Gate Voltage Drain Current      | —    | —    | 25    | μA    | V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V   |
|                                     |                                      | —    | —    | 250   |       | V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C                           |
| I <sub>GSS</sub>                    | Gate-to-Source Leakage Forward       | —    | —    | 100   | nA    | V <sub>GS</sub> = 20V   |
|                                     | Gate-to-Source Leakage Reverse       | —    | —    | -100  |       | V <sub>GS</sub> = -20V  |
| Q <sub>G</sub>                      | Total Gate Charge                    | —    | —    | 59    | nC    | I <sub>D1</sub> = 16A   |
| Q <sub>GS</sub>                     | Gate-to-Source Charge                | —    | —    | 12    |       | V <sub>DS</sub> = 50V   |
| Q <sub>GD</sub>                     | Gate-to-Drain ('Miller') Charge      | —    | —    | 30.7  |       | V <sub>GS</sub> = 10V   |
| t <sub>d(on)</sub>                  | Turn-On Delay Time                   | —    | —    | 21    | ns    | V <sub>DD</sub> = 50V   |
| t <sub>r</sub>                      | Rise Time                            | —    | —    | 145   |       | I <sub>D1</sub> = 16A   |
| t <sub>d(off)</sub>                 | Turn-Off Delay Time                  | —    | —    | 64    |       | R <sub>G</sub> = 9.1Ω   |
| t <sub>f</sub>                      | Fall Time                            | —    | —    | 105   |       | V <sub>GS</sub> = 10V   |
| L <sub>S</sub> + L <sub>D</sub>     | Total Inductance                     | —    | 6.8  | —     | nH    | Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package) |
| C <sub>iss</sub>                    | Input Capacitance                    | —    | 1660 | —     | pF    | V <sub>GS</sub> = 0V  |
| C <sub>oss</sub>                    | Output Capacitance                   | —    | 550  | —     |       | V <sub>DS</sub> = 25V   |
| C <sub>rss</sub>                    | Reverse Transfer Capacitance         | —    | 120  | —     |       | f = 1.0MHz  |

### Source-Drain Diode Ratings and Characteristics

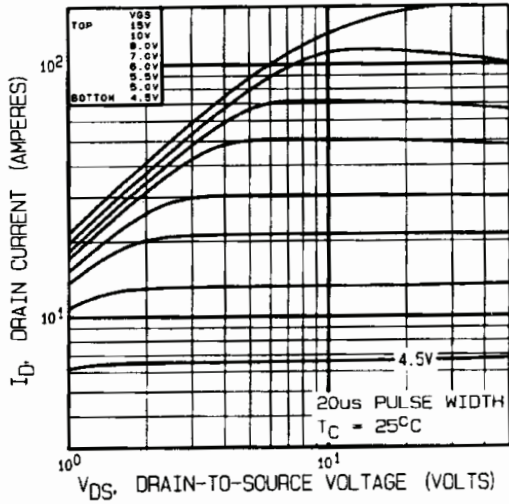
| Symbol          | Parameter                              | Min.   | Typ. | Max. | Units | Test Conditions   |
|-----------------|--|--|------|------|-------|---|
| I <sub>S</sub>  | Continuous Source Current (Body Diode) | —  | —    | 16   | A     |   |
| I <sub>SM</sub> | Pulsed Source Current (Body Diode) ①   | —  | —    | 100  |       |   |
| V <sub>SD</sub> | Diode Forward Voltage                  | —  | —    | 1.5  | V     | T <sub>J</sub> = 25°C, I <sub>S</sub> = 16A, V <sub>GS</sub> = 0V ④ |
| t <sub>rr</sub> | Reverse Recovery Time                  | —  | —    | 400  | ns    | T <sub>J</sub> = 25°C, I <sub>F</sub> = 16A, V <sub>DD</sub> ≤ 50V  |
| Q <sub>rr</sub> | Reverse Recovery Charge                | —  | —    | 2.4  | μC    | di/dt = 100A/μs ④   |
| T <sub>on</sub> | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> ) |      |      |       |   |

### Thermal Resistance

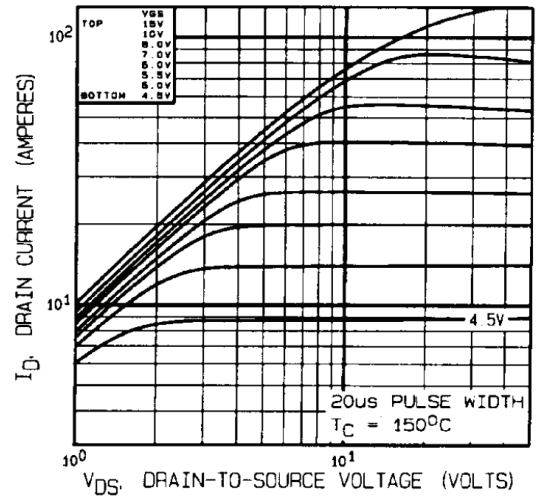
| Symbol           | Parameter                                  | Min. | Typ. | Max. | Units |
|------------------|--|------|------|------|-------|
| R <sub>θJC</sub> | Junction-to-Case                           | —    | —    | 1.25 | °C/W  |
| R <sub>θCS</sub> | Case-to-sink                               | —    | 0.21 | —    |       |
| R <sub>θJA</sub> | Junction-to-Ambient (Typical Socket Mount) | —    | —    | 80   |       |

#### Footnotes:

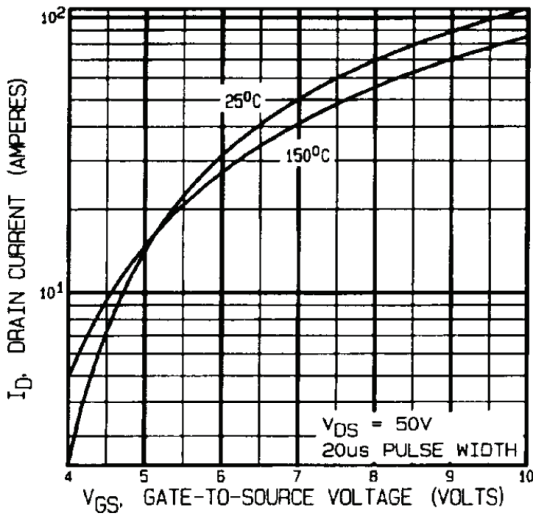
- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 1.8mH, Peak I<sub>L</sub> = 16A, V<sub>GS</sub> = 10V.
- ③ I<sub>SD</sub> ≤ 16A, di/dt ≤ 170A/μs, V<sub>DD</sub> ≤ 100V, T<sub>J</sub> ≤ 150°C.
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%



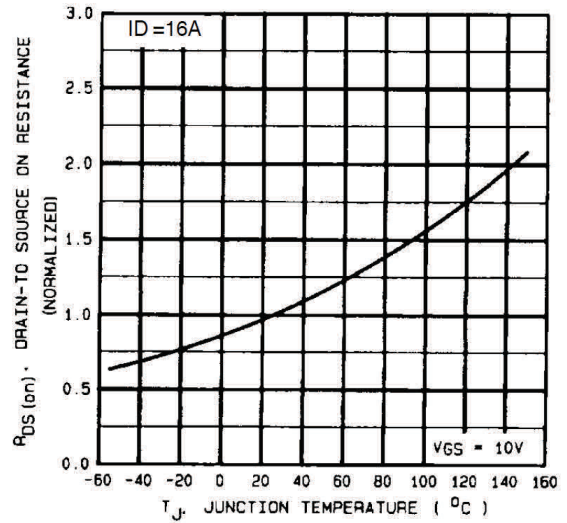
**Fig 1.** Typical Output Characteristics



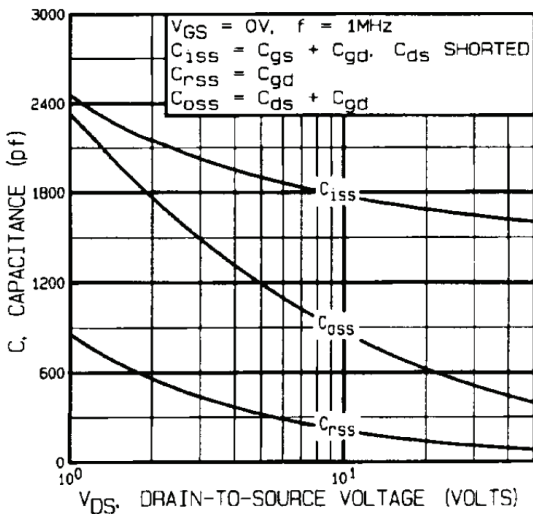
**Fig 2.** Typical Output Characteristics



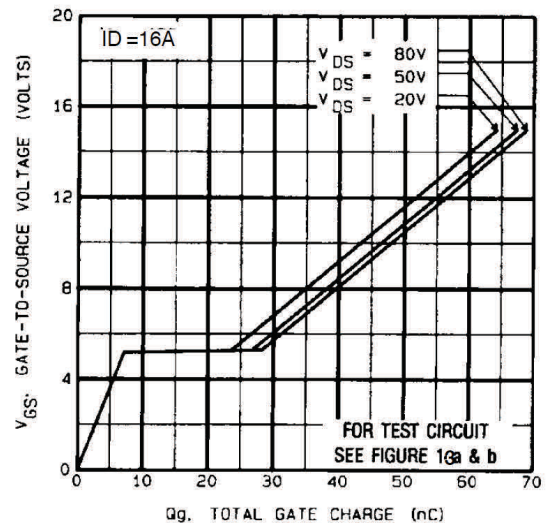
**Fig 3.** Typical Transfer Characteristics



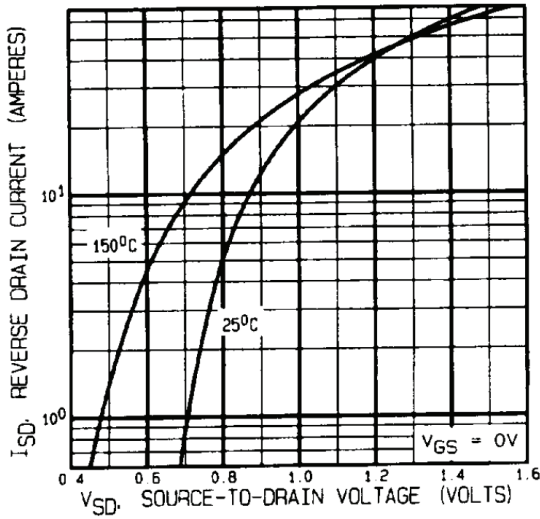
**Fig 4.** Normalized On-Resistance Vs. Temperature



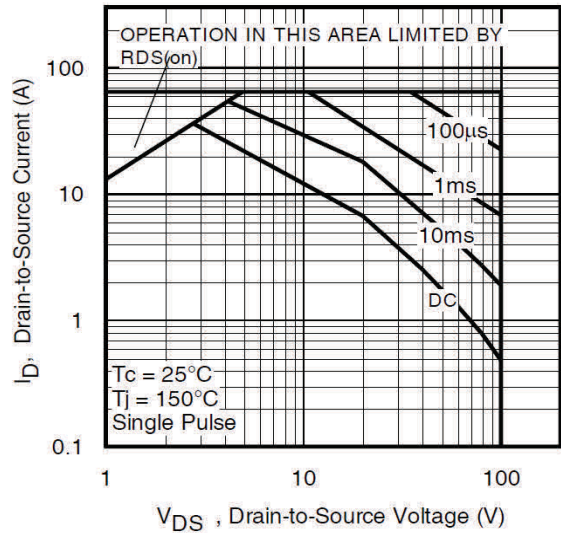
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



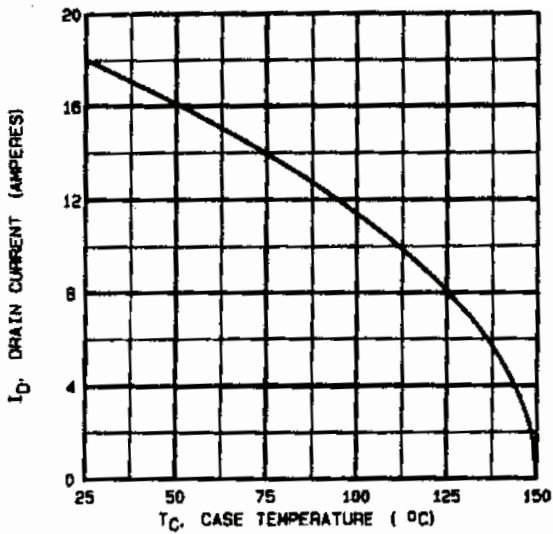
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



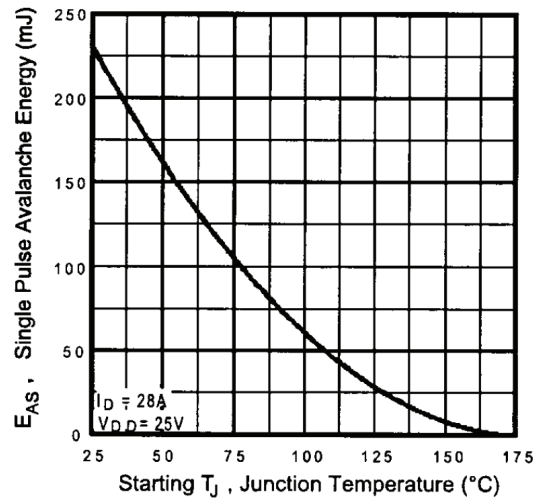
**Fig 7.** Typical Source-Drain Diode Forward Voltage



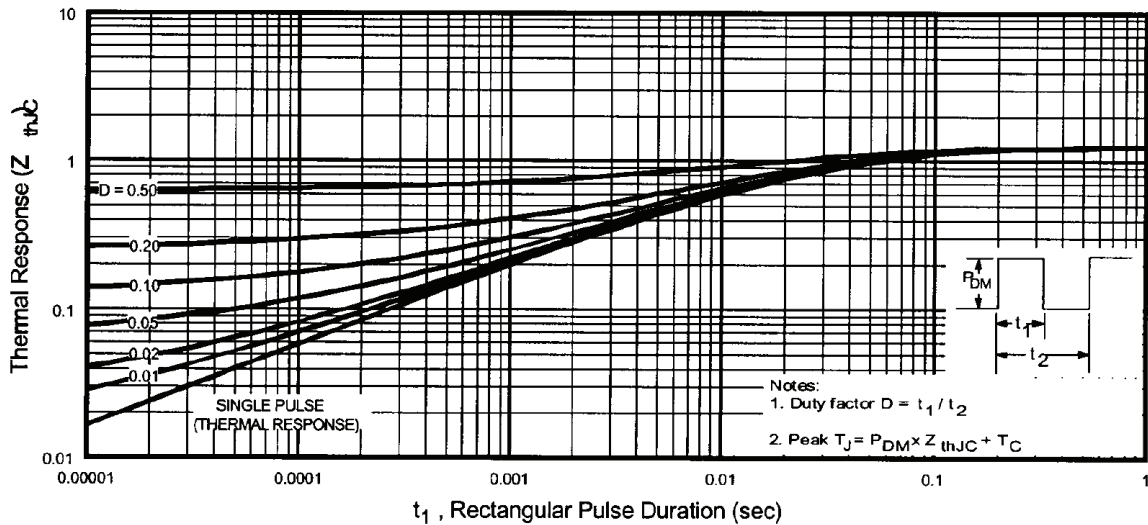
**Fig 8.** Maximum Safe Operating Area



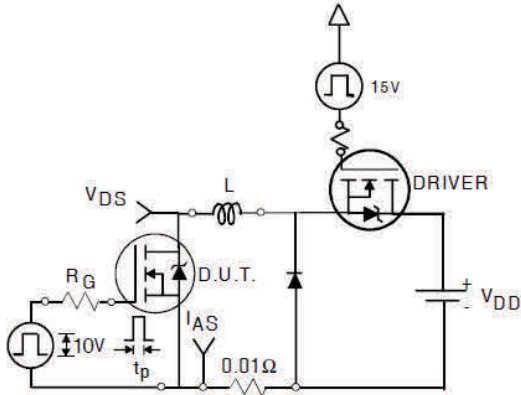
**Fig 9.** Maximum Drain Current Vs. Case Temperature



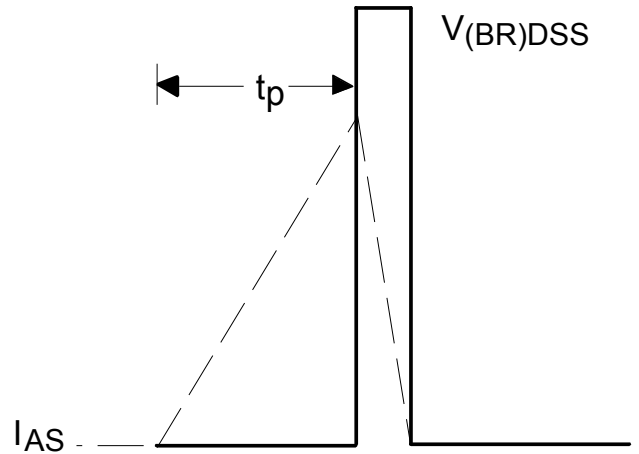
**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



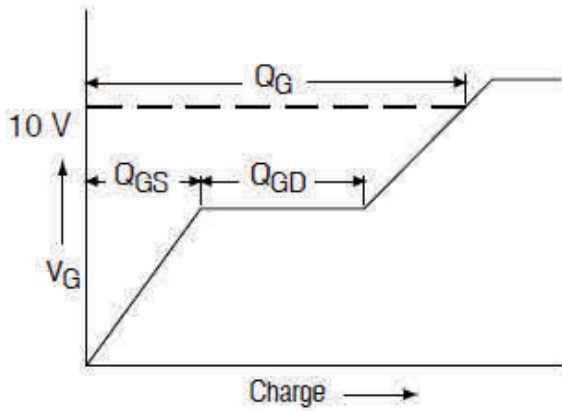
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



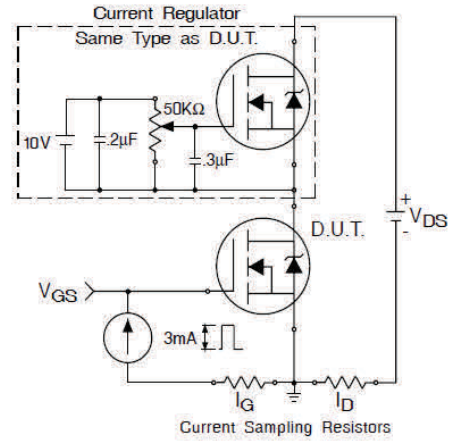
**Fig 12a.** Unclamped Inductive Test Circuit



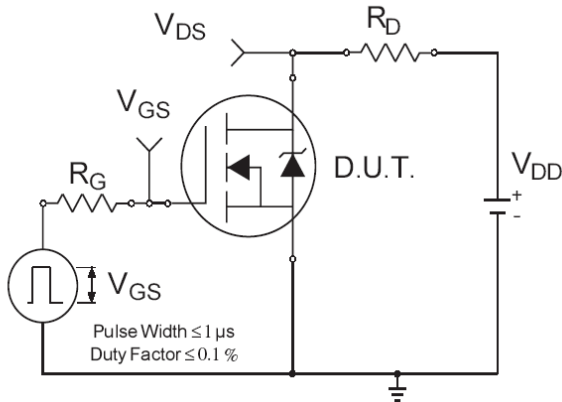
**Fig 12b.** Unclamped Inductive Waveforms



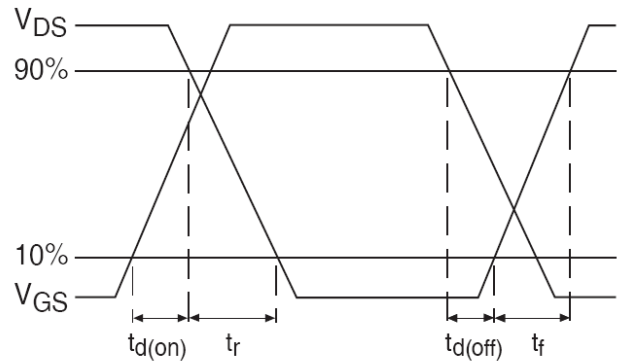
**Fig 13a.** Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

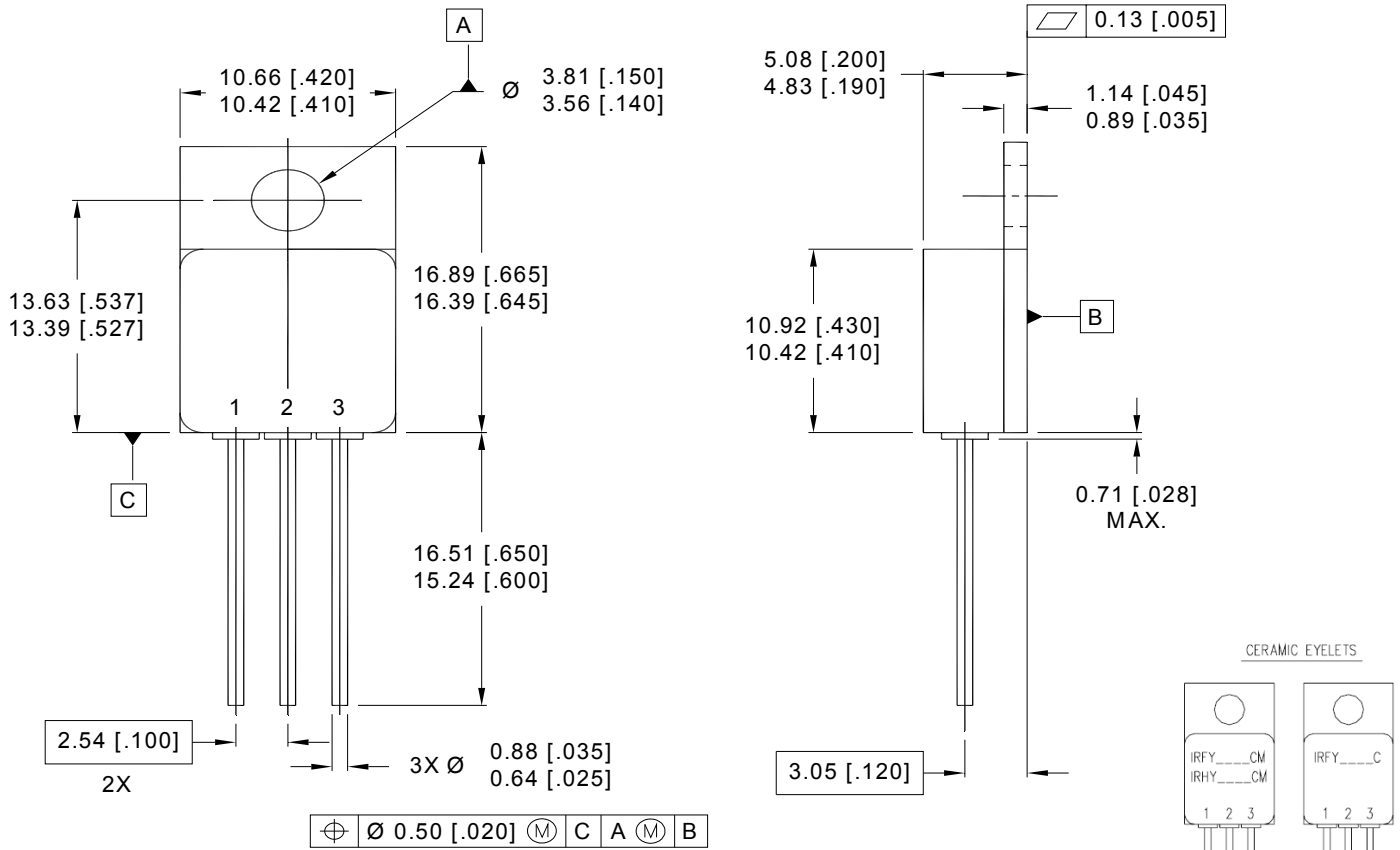


**Fig 14a.** Switching Time Test Circuit



**Fig 14b.** Switching Time Waveforms

**Case Outline and Dimensions - TO257AA**

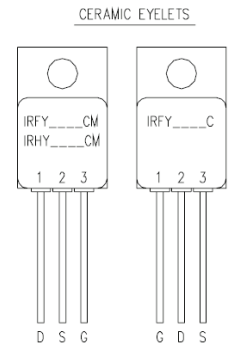


**NOTES:**

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.

**LEAD ASSIGNMENT**

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE



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